

### 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Low threshold voltage
- Trench MOSFET technology
- Side wettable flanks for optical solder inspection
- ElectroStatic Discharge (ESD) protection > 500 V HBM (class H1B)
- AEC-Q101 qualified

### 3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

### 4. Quick reference data

### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	30	V
V <sub>GS</sub>	gate-source voltage			-8	-	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-	5	А
Static chara	cteristics						
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C		-	28	33	mΩ

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

# nexperia

# 5. Pinning information

Table 2. I	Table 2. Pinning information								
Pin	Symbol	Description	Simplified outline	Graphic symbol					
1	D	drain		D					
2	D	drain							
3	G	gate		<sub>G</sub> ∠→ ⊑ 本 )					
4	S	source	3 8 4						
5	D	drain	Transparent top view						
6	D	drain	DFN2020MD-6	s					
7	D	drain	(SOT1220)	017aaa255					
8	S	source							

## 6. Ordering information

### Table 3. Ordering information

Type number	e number Package					
	Name	Description	Version			
PMPB29XNEA		DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220			

## 7. Marking

Table 4. Marking codes	
Type number	Marking code
PMPB29XNEA	4H

### 8. Limiting values

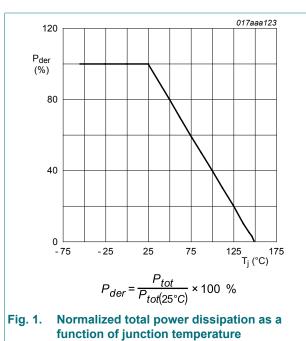
#### Table 5. Limiting values

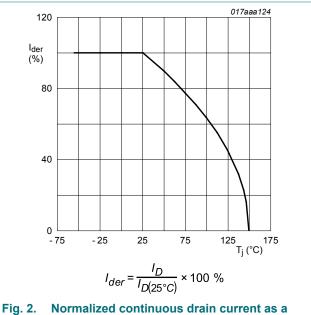
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	30	V
V <sub>GS</sub>	gate-source voltage	-		-8	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	5	А
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	3.2	А
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	12	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[1]	-	1.7	W
		T <sub>sp</sub> = 25 °C		-	12.5	W
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drai	n diode				-	
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	1.9	А
ESD maxim	um rating					
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[2]	-	500	V
Avalanche r	ruggedness					1
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$T_{j(init)} = 25 \text{ °C; } I_D = 0.75 \text{ A; DUT in}$ avalanche (unclamped)		-	11.8	mJ

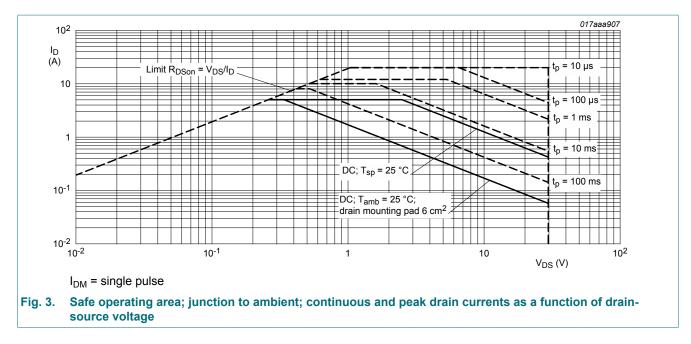
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

[2] Measured between all pins.





### 30 V, N-channel Trench MOSFET

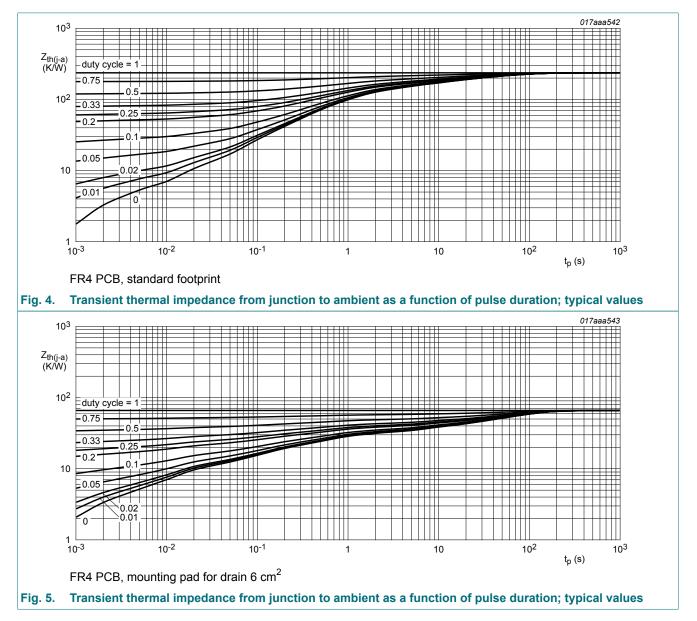


### 9. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient	thermal resistance from	in free air	[1]	-	235	270	K/W
		[2]	-	67	74	K/W	
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	5	10	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

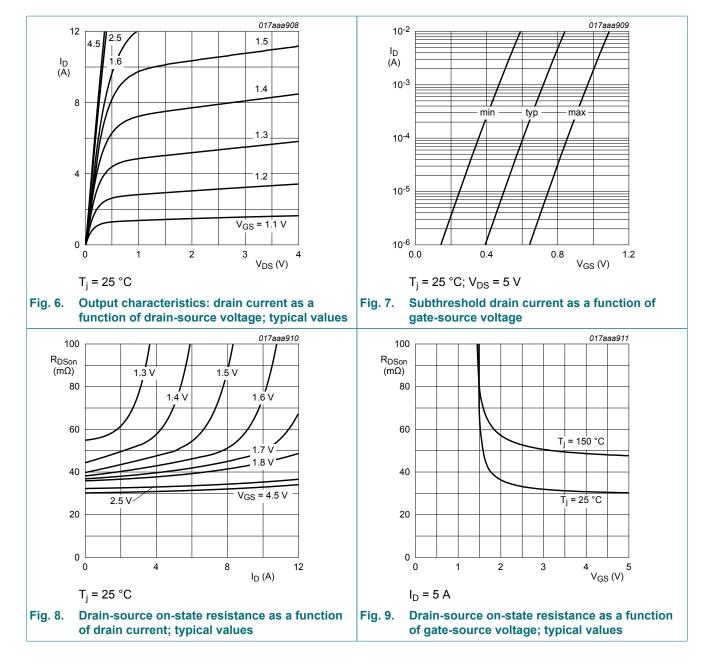
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



## **10. Characteristics**

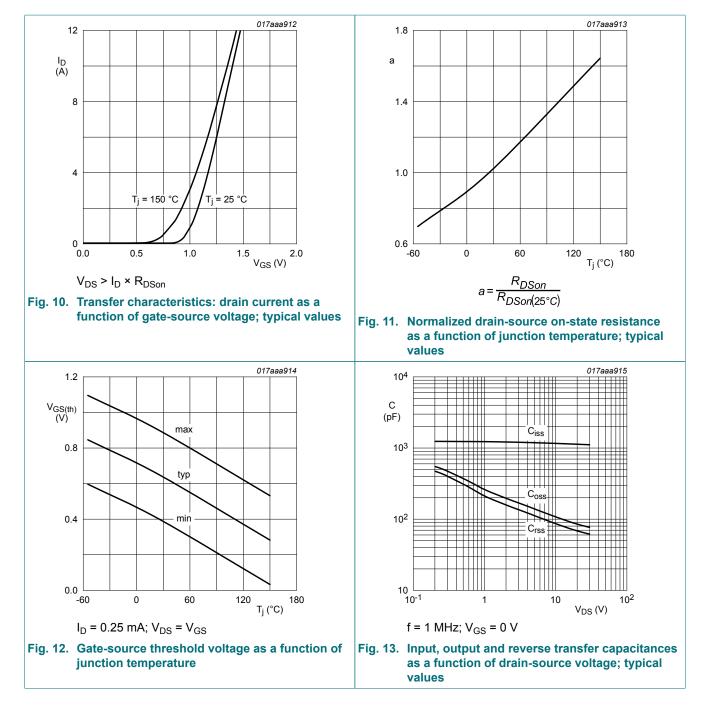
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	octeristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	30	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	$I_D$ = 250 µA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	0.4	0.65	0.9	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 20 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	-	1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		V <sub>GS</sub> = -8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C	-	28	33	mΩ
	resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 150 °C	-	46	54	mΩ
		V <sub>GS</sub> = 2.5 V; I <sub>D</sub> = 3 A; T <sub>j</sub> = 25 °C	-	32	40	mΩ
		V <sub>GS</sub> = 1.8 V; I <sub>D</sub> = 1.9 A; T <sub>j</sub> = 25 °C	-	37	50	mΩ
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C	-	30	-	S
R <sub>G</sub>	gate resistance	f = 1 MHz; T <sub>i</sub> = 25 °C	-	1.8	-	Ω
Dynamic ch	aracteristics		I			
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 15 V; I <sub>D</sub> = 5 A; V <sub>GS</sub> = 4.5 V;	-	12.4	18.6	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	1.2	-	nC
Q <sub>GD</sub>	gate-drain charge	-	-	2.1	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 15 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	1150	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	110	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	85	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 15 V; I <sub>D</sub> = 5 A; V <sub>GS</sub> = 4.5 V;	-	8	-	ns
t <sub>r</sub>	rise time	R <sub>G(ext)</sub> = 6 Ω; T <sub>j</sub> = 25 °C	-	17	-	ns
t <sub>d(off)</sub>	turn-off delay time	-	-	33	-	ns
t <sub>f</sub>	fall time	-	-	32	-	ns
Source-drai	n diode		I		-	
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 1.9 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.6	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 1.9 A; dI <sub>S</sub> /dt = -100 A/μs;	-	9	-	ns
Q <sub>r</sub>	recovered charge	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 15 V; T <sub>j</sub> = 25 °C	-	2	-	nC

#### 30 V, N-channel Trench MOSFET

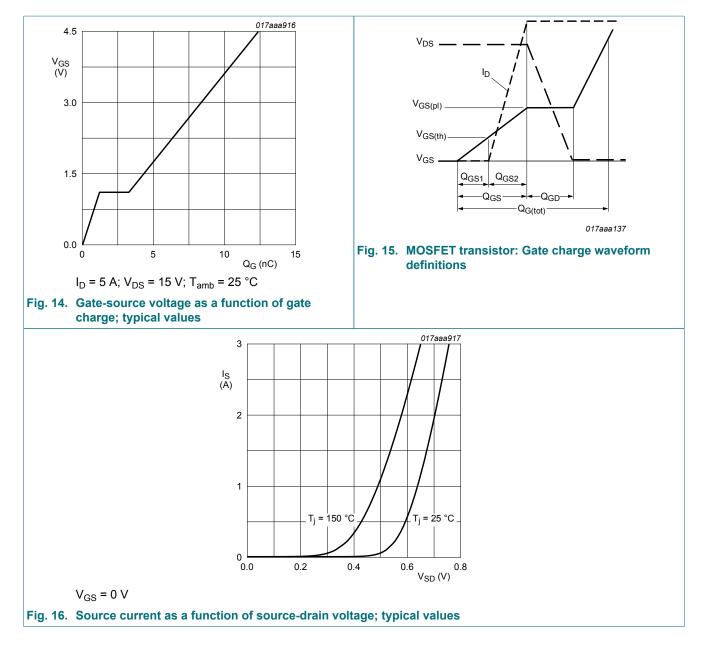


**Product data sheet** 

#### 30 V, N-channel Trench MOSFET

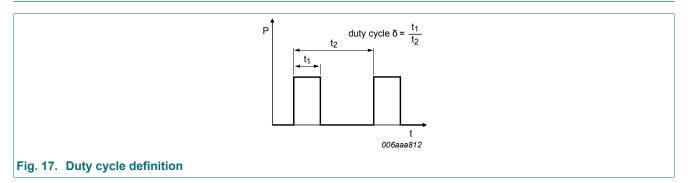


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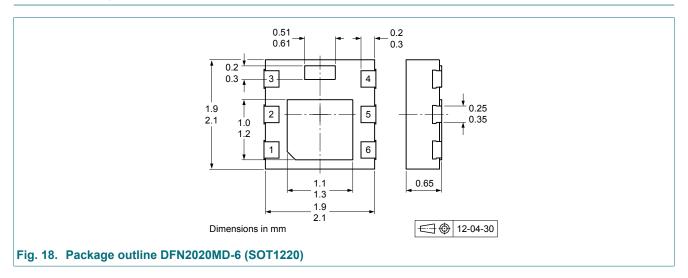
### **11. Test information**



### **Quality information**

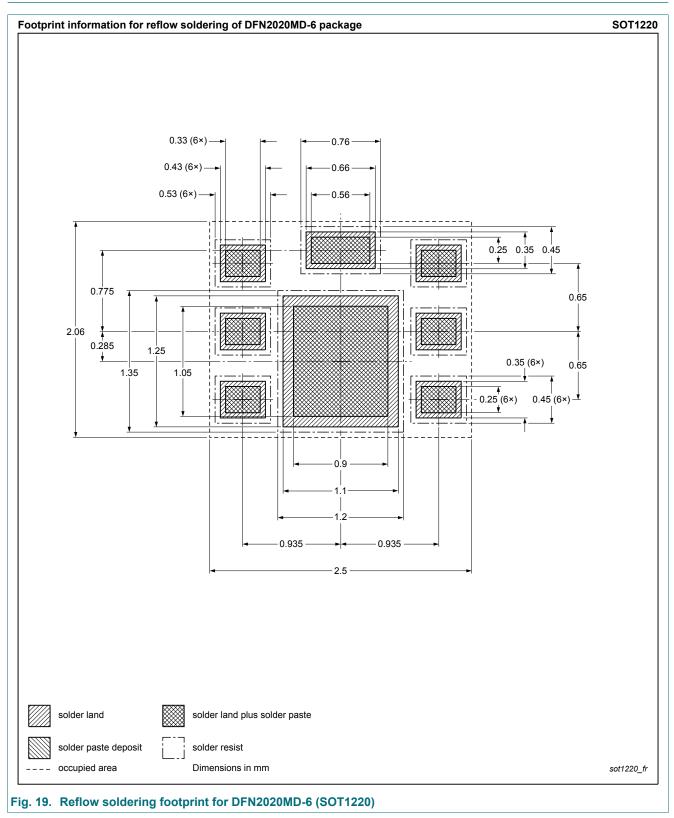
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

### 12. Package outline



### 30 V, N-channel Trench MOSFET

### 13. Soldering



# 14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PMPB29XNEA v.1	20180910	Product data sheet	-	-		

## 15. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

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